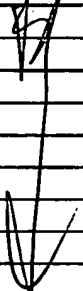



FORM: PTO-1449 (REV: 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	Atty Docket No: 2000-0719.01/US	Serial No: Not Assigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (37 CFR 1.98(b)) (use several sheets if necessary)		Applicant: Micron Technology, Inc.	
		Filing Date: September 8, 2003	Group: Not Assigned



## U.S. PATENT DOCUMENTS


Examiner Initial	Document Number		Date	Name	Class	Subclass	
	AA	5,852,307	12/1998	Aoyama et al.	257	205	
	AB	6,037,206	03/2000	Huang et al.	438	240	
	AC	6,278,152	08/2001	Hieda et al.	257	306	
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	AE	6,475,854	11/2002	Narwankar et al.	438	238	
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	AG						
	AH						
	AI						
	AJ						
AK							

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AL					<input type="checkbox"/>	<input type="checkbox"/>
	AM					<input type="checkbox"/>	<input type="checkbox"/>
	AN					<input type="checkbox"/>	<input type="checkbox"/>

## OTHER ART (including author, title, date, pertinent pages, etc.)

Initial		
	AO	"In-situ Barrier Formation for High Reliable W/Barrier/poly-Si Gate Using Denudation of WNX on Polycrystalline Si", Byung Hak Lee et al., R & D Division, LG Semicon Co. Ltd., 1 Hyangjeong-dong, Cheongju-si, 361-480, Korea, 9/98.
	AP	"Tungsten Gate Structure Formed by Reduced Temperature Conversion of Tungsten Nitride", C.J. Galewski et al., Genus Inc. pp 1-2 no date available
	AQ	Copending Application: "Method for Forming and Integrated Circuit Structures Containing Ruthenium and Tungsten Containing Layers", Serial Number 09/590,795, Docket Number 6047-53173, Filed June 8, 2000.
	AR	→ <del>NOT</del> NOT A PUBLICATION

Examiner: 	Date Considered: 6/27/03
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.